

10. (Three Times Amended) An ohmic electrode obtained by annealing a multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprising In and a film including at least a metal nitride film which are sequentially stacked on a III-V compound semiconductor body, wherein said metal nitride film is selected from the group consisting of a WSiN film, a TaN film, a TaSiN film, a TiN film, a TiSiN film, and a TiON film.

17. (Amended) The ohmic electrode according to claim 14 obtained by annealing said multi-layered structure for fabricating an ohmic electrode in which said metal film is one of a Ni film, a Co film, and an Al film.

19. (Three Times Amended) An ohmic electrode provided on a III-V compound semiconductor body obtained by annealing a multi-layered structure for fabricating an ohmic electrode, comprising a non-single crystal semiconductor layer comprised of In and a film including at least a metal nitride film,

the energy barrier between said non-single crystal semiconductor layer and said film being lower than the energy barrier between said III-V compound semiconductor body and said film, wherein said metal nitride film is selected from the group consisting of a WSiN film, a TaN film, a TaSiN film, a TiN film, a TiSiN film, and a TiON film.

REMARKS

Claims 1-19 are pending in the application. In the Office Action of May 8, 2002, the Examiner made the following disposition:

- A.) Objected to claims 7 and 17.
- B.) Rejected claims 1-3, 9-13, and 19 under 35 U.S.C. §103(a) as being unpatentable over *Jackson et al.* in view of *Twynam et al.*
- C.) Rejected claims 4-8 and 14-18 under 35 U.S.C. §103(a) as being unpatentable over *Jackson et al.* in view of *Twynam et al.*, and further in view of *Nirschl et al.*

Applicants respectfully traverse the rejections and address the Examiner's disposition as follows: